

Theory II: transport and mechanics

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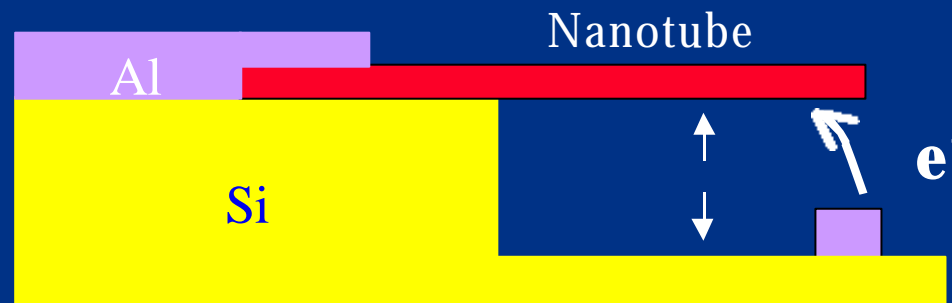
Outline

1. Nanoelectromechanical devices
(J.K., S. Viefers, T. Johansson [M.Sc. Thesis])
2. Nanotube SET
(J.K., Jaeuk Kim, Ilya Krive)
3. Other projects
(Andreas Hall [M.Sc. thesis], Elisabetta Inglessi [M.Sc. thesis])

Nanoelectromechanical devices

- Discrete charge redistribution on the nanometer scale creates large Coulomb forces
 - Electronic transport is highly sensitive to mechanical deformations
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Nanorelay (2-terminal)



$$\tau_R = RC \sim 10^{-11} - 10^{-12} \text{ s}$$

$$\tau_{\text{elastic}} \sim 10^{-11} - 10^{-12} \text{ s}$$

Tunnel junction with dynamically varying geometry

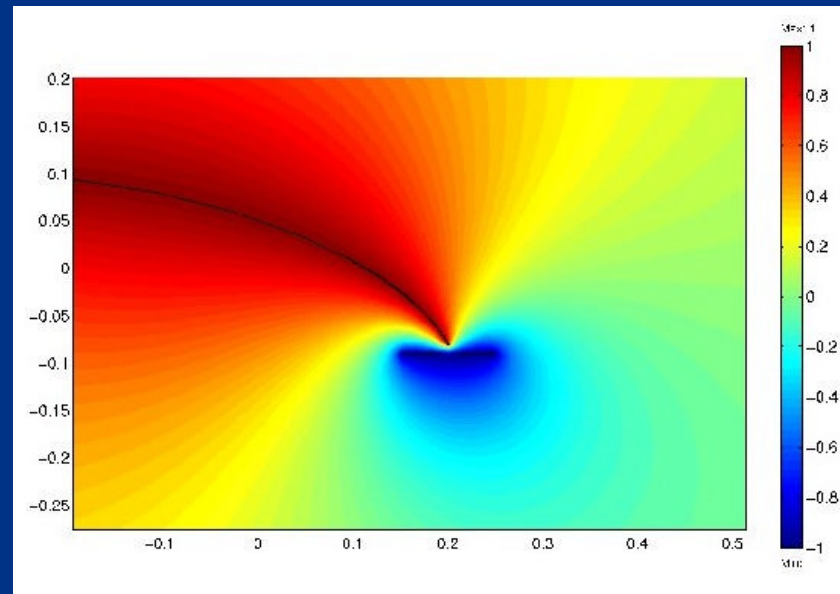
⇒ variable tunneling resistance and capacitance:

(x = tube displacement, h = maximum displacement)

$$R_T(x) = R_T(x=h) \exp[-\alpha(h-x)]$$

$$C(x) \approx C(x=h)/(d-x) \quad (\text{determined numerically})$$

Additional parameters: tube length, contact resistance,...

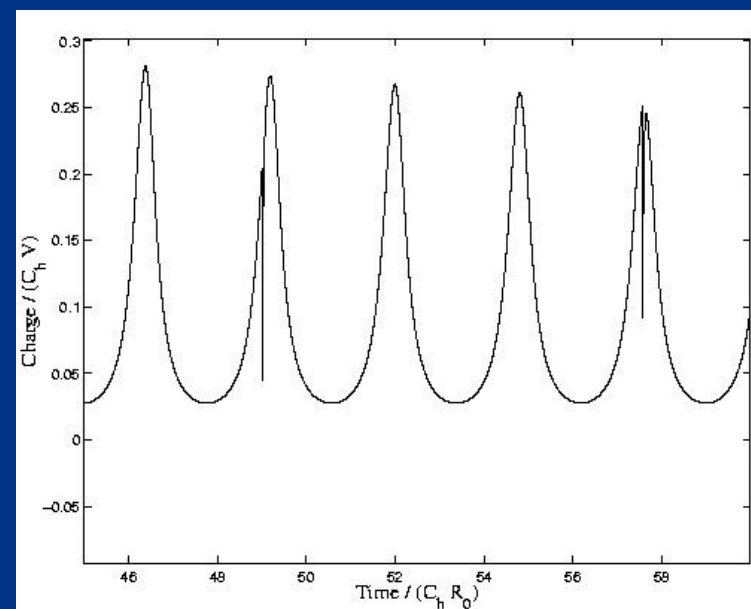
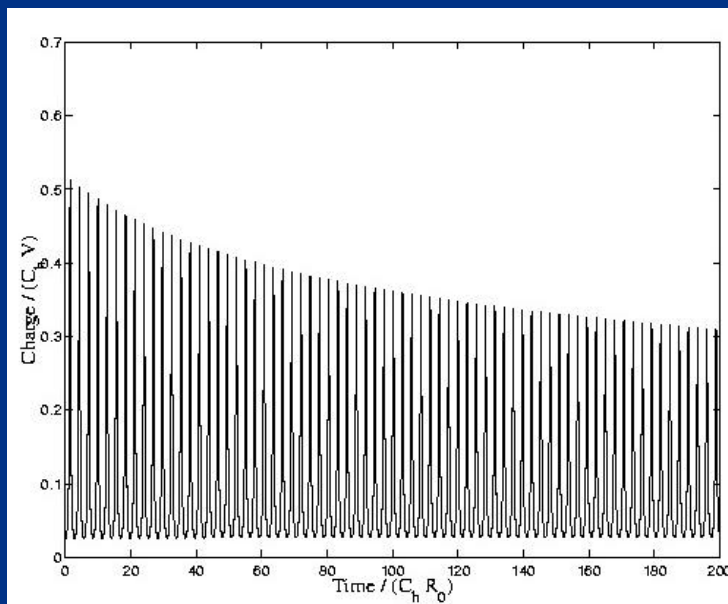


Methods:

1. Classical circuit analysis (*large tunneling current limit*)
 - mechanical motion described using classical elasticity theory
 - charge granularity and electron correlations ignored
2. Stochastic tunneling analysis
 - mechanical motion described using classical elasticity theory
 - electron correlations ignored
3. Microscopic model
 - mechanical motion described by a single harmonic oscillator
 - damping ignored, tube approximated as a semi-infinite LL

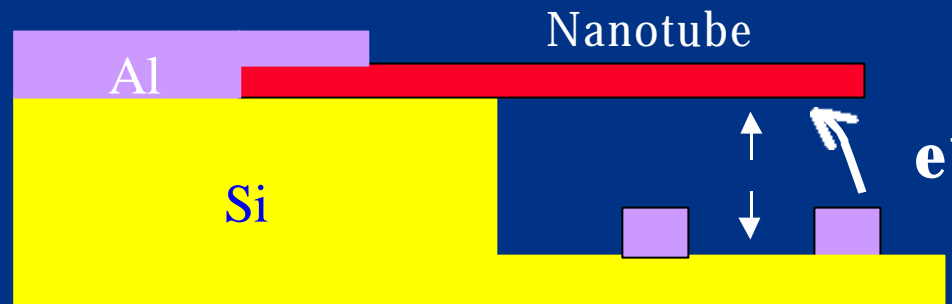
Results:

- realistic values for the contact resistance lead to significant damping
- for realistic parameters, the effect of electron tunneling on tube motion (*the kick-back effect*) is small
- the microscopic model leads to a modified Tien-Gordon model for phonon-assisted tunneling



What next:

3-terminal device



- device geometry controlled by gate voltage
- allows for small source-drain voltages, and small power consumption
- study switching characteristics and damping

Nanotube SET

Experiment:

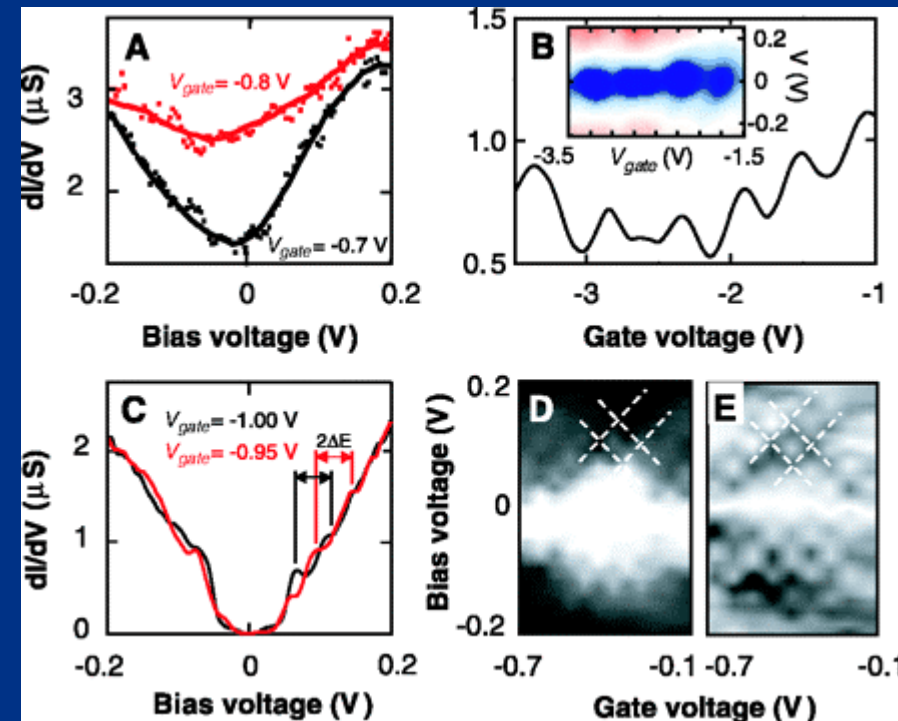
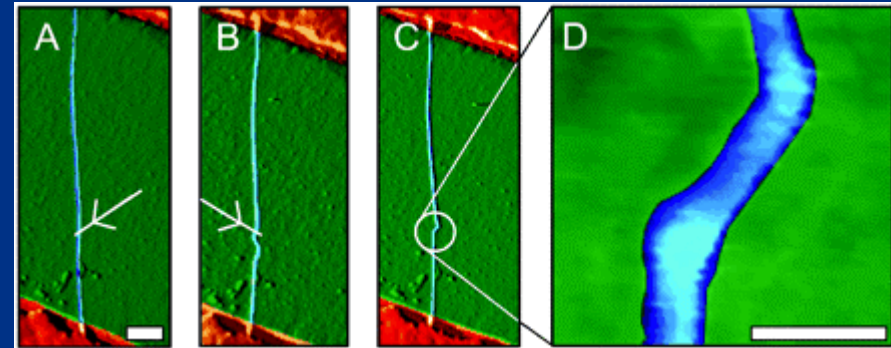
H. W. Ch. Postma, T. Teepen, Z. Yao, M. Grifoni, and C. Dekker,
Science 293, 76 (2001)

Theory:

- developed for uncorrelated systems
- a $T=0$, $V=0$ theory exists for correlated systems

Our approach:

- sequential tunneling through a finite LL segment
- finite T and V
- analytic calculation of tunneling rates (*finished*), numerical solution of master equation



Other projects

Magnetic field effects on nanotubes

- A. Hall, M.Sc. thesis
- transverse magnetic field induces a gap in metallic zigzag tubes $(3n,0)$

Transport measurements in carbon nanotubes

- E. Inglessi, M.Sc. thesis (NPL, London)
- focused on AFM manipulation of tubes